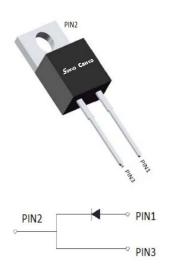


Silicon Carbide Schottky Diode

V_{RRM}	650V
I _{F (135°C)}	3.6A
Qc	5.2nC



Faaturas

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery voltage
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

• Package: TO-220AC

Molding compound meets UL 94 V-0 flammability

rating, -, halogen-free
• Terminals: Tin plated leads
• Polarity: As marked

■Maximum Ratings (T_c=25°C Unless otherwise specified)

PARAMTETER	SYMBOL	UNIT	VALUE
Device marking code			D106502PQG3
Reverse voltage (repetitive peak) @ T _j =25°C	V_{RRM}	V	650
Reverse voltage (Surge Peak) @ T _j =25°C	V_{RSM}	V	650
Reverse voltage (DC) @ T _j =25°C	V _{DC}	V	650
Continuous forward current @ T _c =25°C			7.6
Continuous forward current @ T _c =135°C	I _F	Α	3.6
Continuous forward current @ T _c =160°C			2
Non-repetitive peak forward surge current @ T _c =25°C, tp=10ms, Half Sine Wave	I _{FSM}	А	20
Power Dissipation@ T _c =25°C	D	W	45
Power Dissipation@ T₀=110°C	Р _{тот}	VV	19
i²t Value@ Tc=25°C ,tp=10ms	∫i²dt	A ² S	2
Operating junction and Storage temperature range	T_{j} , T_{stg}	°C	-55 to +175



■Electrical Characteristics

PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.				
Famurad valle and draw	W	V _F V	I _F =2A, T _j =25°C	1.5	1.6				
Forward voltage drop	VF		I _F =2A, T _j =175°C	2.2	-				
Poverse leakage current			V _R =650V, T _j =25°C	0.1	10				
Reverse leakage current	I _R	μΑ	V _R =650V, T _j =175°C	1	-				
Total capacitive charge	Qc	nC	V_R =400V, T_j =25°C , QC = $\int_0^{VR}C(V)dV$	5.2	-				
	С	C	С				V _R =0V, f=1MHZ	84	-
Total capacitance				C pF	V _R =200V, f=1MHZ	9.8	-		
									V _R =400V, f=1MHZ
Capacitance Stored Energy	Ec	μJ	V _R =400V	0.6	-				

■Thermal Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Value
Thermal resistance	R _{eJ-C}	°C M	3.33

■Typical Characteristics

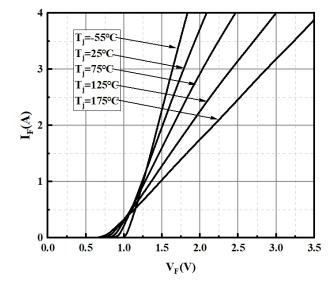


Figure 1. Forward Characteristics

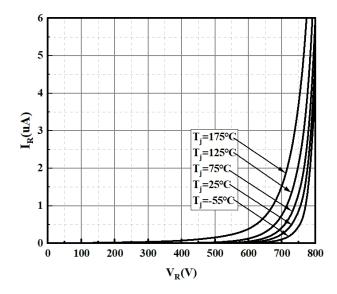
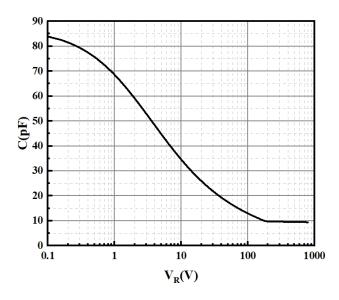


Figure 2. Reverse Characteristic





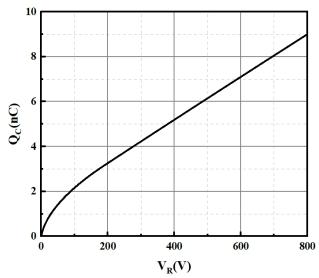
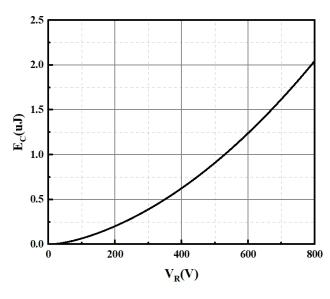


Figure 3. Capacitance vs. Reverse Voltage

Figure 4. Total Capacitance Charge vs. Reverse Voltage



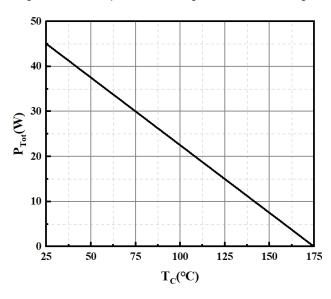
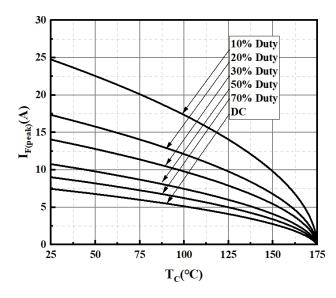


Figure 5. Capacitance Stored Energy

Figure 6. Power Derating



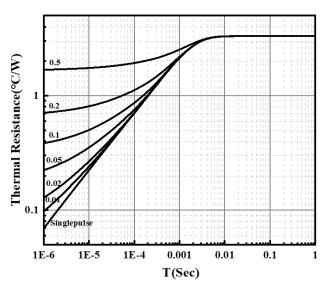
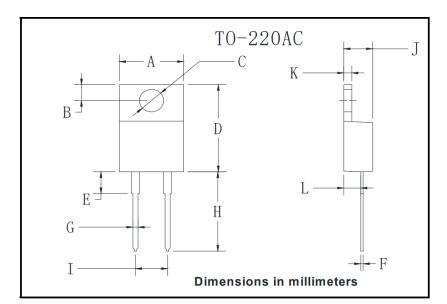


Figure 7. Current Derating

Figure 8. Transient Thermal Impedance



■Outline Dimensions



TO-220AC				
TO-220AC				
Dim	Min	Max		
Α	9.95	10.35		
В	2.55	2.95		
С	3.75	4.05		
D	14.95	15.25		
Е	3.75	4.25		
F	0.26	0.5		
G	0.68	0.94		
Н	13.3	13.9		
I	4.86	5.26		
J	4.38	4.78		
K	1.14	1.4		
L	2.37	2.79		



Disclaimer

The information presented in this document is for reference only. Shanghai Sunco Electronics Co., Ltd reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise.

The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of with would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), Russiansunco or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale.

This publication supersedes & replaces all information previously supplied. For additional information, please visit our website http:// www.russiansunco.com, or consult your nearest Russiansunco's sales office for further assistance.